Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- 1 kV ESD protection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated, 100% solderable side pads for optical solder inspection

3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	11.3	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	13	16	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7 7	
3	G	gate	2 5	$G \left(\begin{array}{c} \downarrow \\ \downarrow \\ \downarrow \end{array} \right)$
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB13XNE	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB13XNE	1M

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	11.3	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	8	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	32	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	liode		'	1	'	
I _S	source current	T _{amb} = 25 °C	[1]	-	2	Α

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

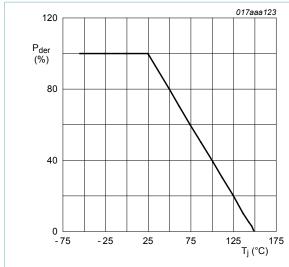


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

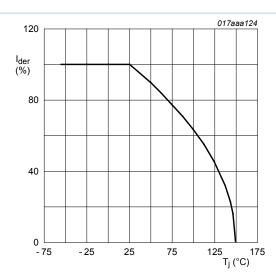


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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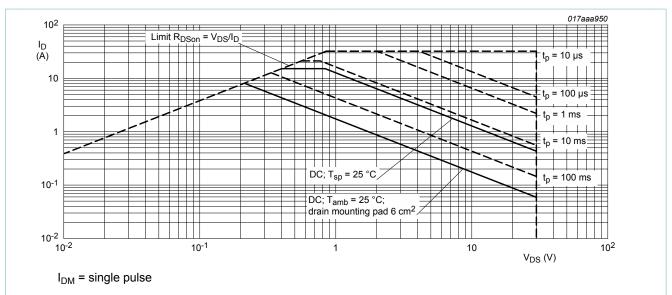


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	_	[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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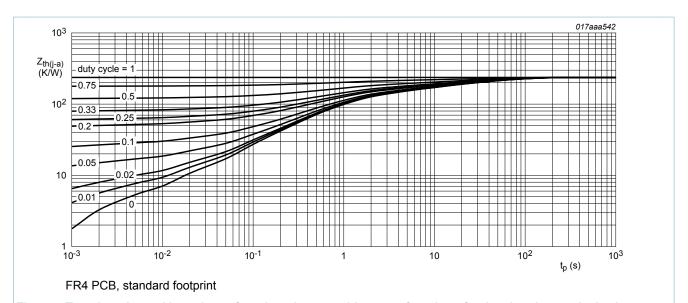


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

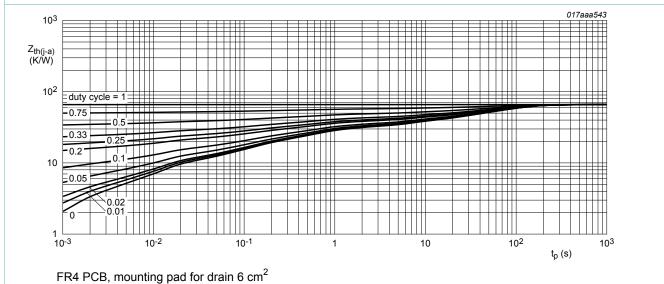


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C	-	13	16	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 8 A; T _j = 150 °C	-	21	27	mΩ
		V _{GS} = 2.5 V; I _D = 7.2 A; T _j = 25 °C	-	14	20	mΩ
		V _{GS} = 1.8 V; I _D = 3.7 A; T _j = 25 °C	-	17	24	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 8 A; T_{j} = 25 °C	-	60	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	2.1	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 6 A; V_{GS} = 4.5 V;	-	24	36	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	2.4	-	nC
Q_{GD}	gate-drain charge		-	4.6	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	2195	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	155	-	pF
C _{rss}	reverse transfer capacitance		-	135	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_{D} = 6 A; V_{GS} = 4.5 V;	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	54	-	ns
t _f	fall time		-	49	-	ns
Source-dra	in diode		<u> </u>		1	
V _{SD}	source-drain voltage	I _S = 2 A; V _{GS} = 0 V; T _i = 25 °C	-	0.6	1.2	V

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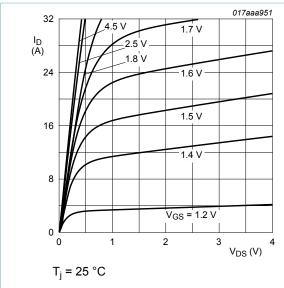


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

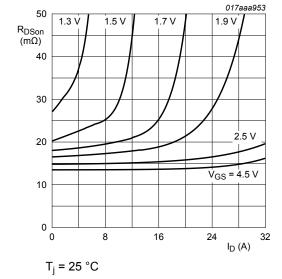


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

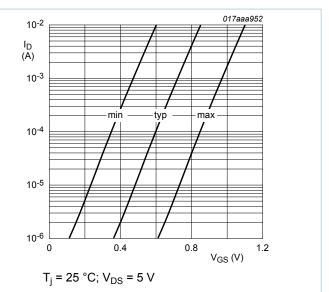


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

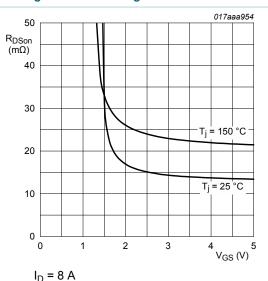


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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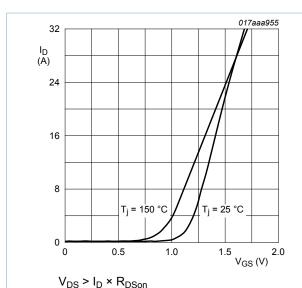


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

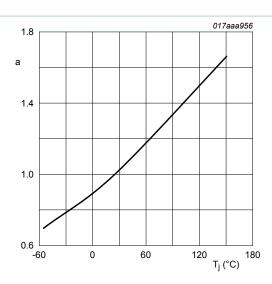


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

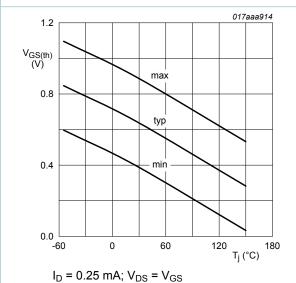


Fig. 12. Gate-source threshold voltage as a function of junction temperature

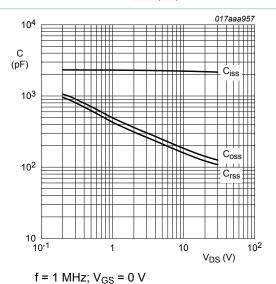


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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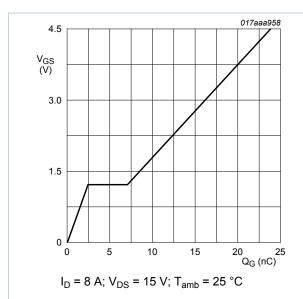


Fig. 14. Gate-source voltage as a function of gate charge; typical values

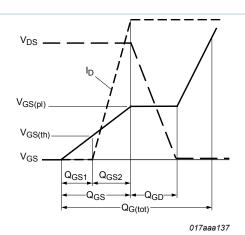


Fig. 15. MOSFET transistor: Gate charge waveform definitions

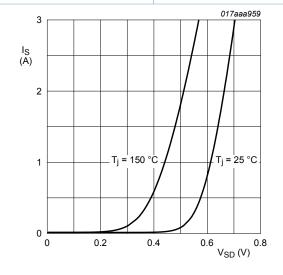
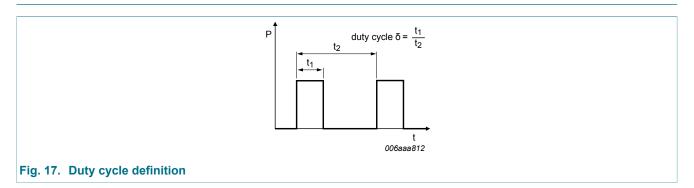


Fig. 16. Source current as a function of source-drain voltage; typical values

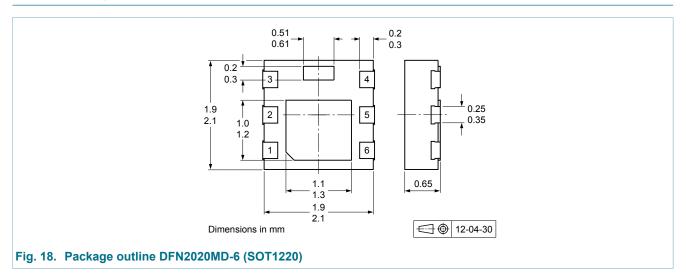
 $V_{GS} = 0 V$

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11. Test information

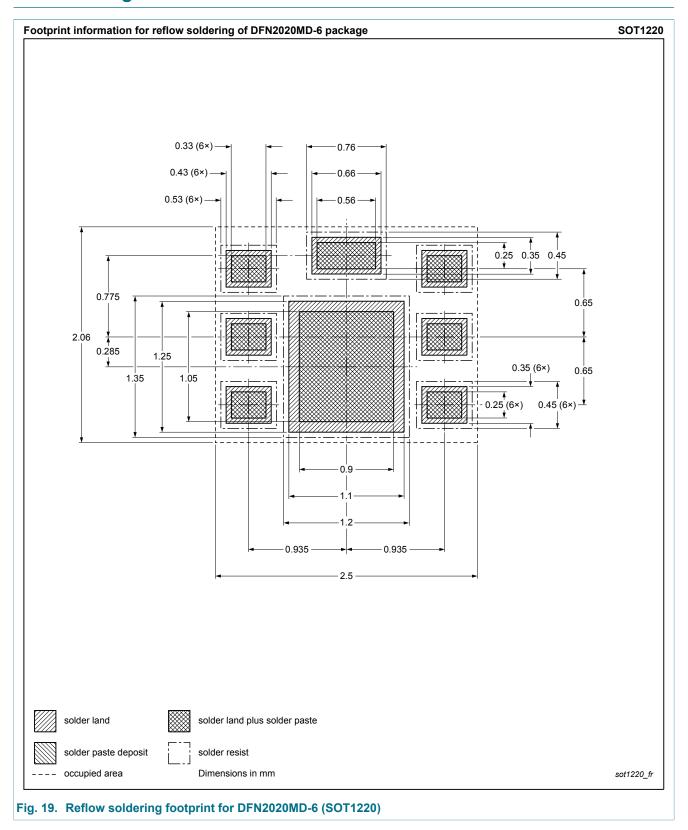


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB13XNE v.2	20141126	Product data sheet	-	PMPB13XNE v.1
Modifications:	 3D package outline Features and benef Table 5: updated			
PMPB13XNE v.1	20121130	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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